

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|------|--|---|------------------|---------|------------------|
| S102 | 14 | (elo or lateral near2 overgrow\$5) same pitch | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/14 01:28 |
| S99 | 36 | S98 and mask\$5 same Gaas | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/14 01:34 |
| S98 | 477 | (kensaku near2 motoki or takuji near2 okahisa or naoki near2 matsumoto).in. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/14 01:34 |
| S96 | 41 | semiconduct\$6 near4 single near2 crystal\$6 near10 cleav\$6 near10 (wafer or substrate) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/14 01:34 |
| S92 | 54 | (gan or gallium near2 nitride) near10 (hvpe or (halide or hydride) near5 vapor near2 epitax\$7) near10 (ingot or bulk) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/14 01:34 |
| L5 | 66 | (gan or gallium near2 nitride) near10 (hvpe or (halide or hydride) near5 vapor near2 epitax\$7) near10 (ingot or bulk) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/14 01:34 |
| L4 | 45 | semiconduct\$6 near4 single near2 crystal\$6 near10 cleav\$6 near10 (wafer or substrate) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/14 01:34 |
| L3 | 46 | L2 and mask\$5 same Gaas | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/14 01:34 |
| L2 | 512 | (kensaku near2 motoki or takuji near2 okahisa or naoki near2 matsumoto).in. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/14 01:34 |
| L1 | 512 | (kensaku near2 motoki or takuji near2 okahisa or naoki near2 matsumoto).in. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/14 01:34 |

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|-----|-----|---|---|----|----|------------------|
| S59 | 7 | mask near10 pattern\$6 near10 pitch near10 direction near10 parallel | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/14 01:35 |
| S24 | 195 | (stripe mask\$4 or pattern\$6) near15 direction and (gan or gallium near2 nitride) near10 epitax\$7 and (gaas or gallium near2 arsenide) near10 substrate | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/14 01:35 |
| L7 | 235 | (stripe mask\$4 or pattern\$6) near15 direction and (gan or gallium near2 nitride) near10 epitax\$7 and (gaas or gallium near2 arsenide) near10 substrate | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/14 01:35 |
| L6 | 9 | mask near10 pattern\$6 near10 pitch near10 direction near10 parallel | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/11/14 01:35 |